



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

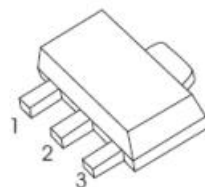
CXT5551

SOT-89 Bipolar Transistor 双极型三极管

■ Features 特点

NPN High Voltage 高压

- 1. BASE
- 2. COLLECTOR
- 3. EMITTER



■ Absolute Maximum Ratings 最大额定值

| Characteristic 特性参数 | Symbol 符号 | Rat 额定值 | Unit 单位 |
|---|-----------------------------|----------------------------|---------------------------|
| Collector-Base Voltage 集电极基极电压 | V_{CBO} | 180 | V |
| Collector-Emitter Voltage 集电极发射极电压 | V_{CEO} | 160 | V |
| Emitter-Base Voltage 发射极基极电压 | V_{EBO} | 6 | V |
| Collector Current 集电极电流 | I_C | 600 | mA |
| Power dissipation 耗散功率 | $P_C(T_a=25^\circ\text{C})$ | 500 | mW |
| Thermal Resistance Junction-Ambient 热阻 | $R_{\theta JA}$ | 250 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature 结温和储藏温度 | T_J, T_{stg} | -55to+150 $^\circ\text{C}$ | |

■ Device Marking 产品打标

CXT5551=1G6

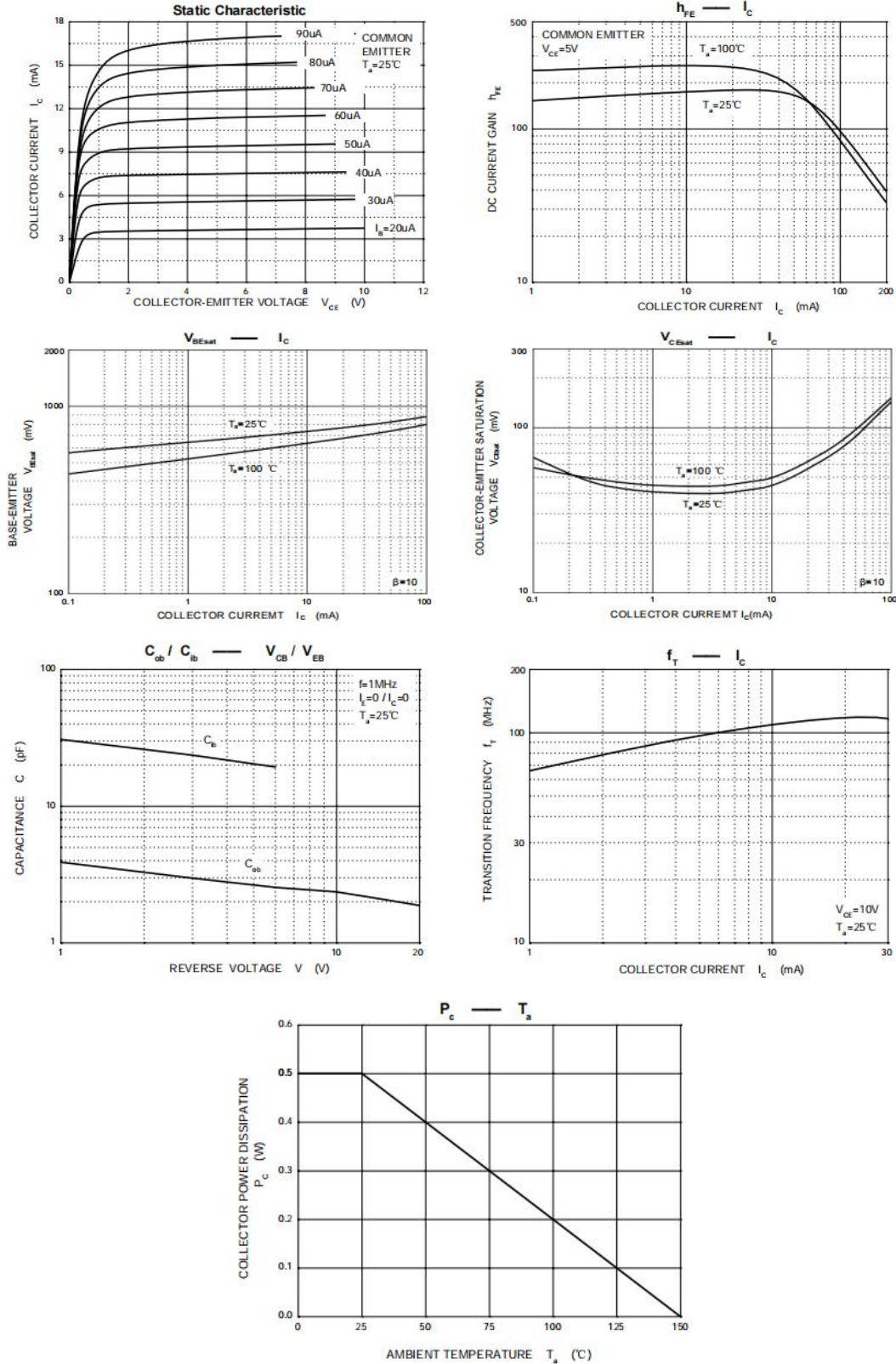


■ Electrical Characteristics 电特性

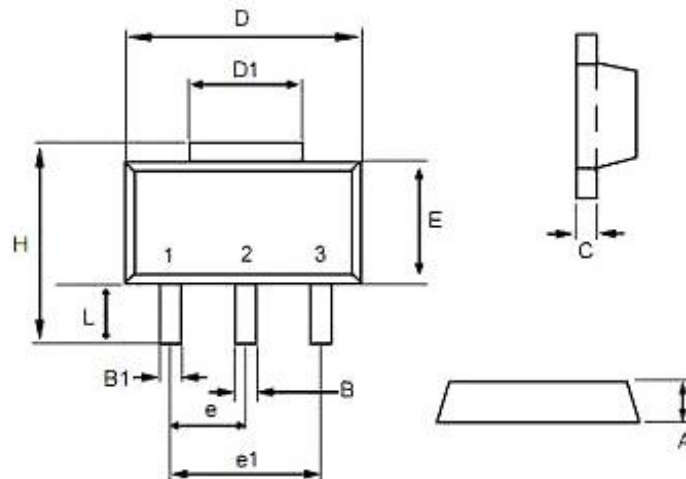
(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

| Characteristic 特性参数 | Symbol 符号 | Min 最小值 | Type 典型值 | Max 最大值 | Unit 单位 |
|--|----------------------|------------|-------------|-------------|------------|
| Collector-Base Breakdown Voltage 集电极基极击穿电压(I _C =100uA, I _E =0) | BV _{CBO} | 180 | — | — | V |
| Collector-Emitter Breakdown Voltage 集电极发射极击穿电压(I _C =1mA, I _B =0) | BV _{CEO} | 160 | — | — | V |
| Emitter-Base Breakdown Voltage 发射极基极击穿电压(I _E =10uA, I _C =0) | BV _{EBO} | 6 | — | — | V |
| Collector-Base Leakage Current 集电极基极漏电流(V _{CB} =180V, I _E =0) | I _{CBO} | — | — | 100 | nA |
| Collector-Emitter Leakage Current 集电极发射极漏电流(V _{CE} =120V, I _B =0) | I _{CEO} | — | — | 100 | nA |
| Emitter-Base Leakage Current 发射极基极漏电流(V _{EB} =6V, I _C =0) | I _{EBO} | — | — | 100 | nA |
| DC Current Gain 直流电流增益(V _{CE} =5V, I _C =1mA) | H _{FE} (1) | 80 | — | — | |
| DC Current Gain 直流电流增益(V _{CE} =5V, I _C =10mA) | H _{FE} (2) | 100 | — | 300 | |
| DC Current Gain 直流电流增益(V _{CE} =5V, I _C =100mA) | H _{FE} (3) | 30 | — | — | |
| Collector-Emitter Saturation Voltage 集电极发射极饱和压降(I _C =10mA, I _B =1mA) (I _C =50mA, I _B =5mA) | V _{CE(sat)} | — | — | 0.15 0.2 | V |
| Base-Emitter Saturation Voltage 基极发射极饱和压降(I _C =10mA, I _B =1mA) (I _C =50mA, I _B =5mA) | V _{BE(sat)} | — | — | 1 1 | V |
| Transition Frequency 特征频率(V _{CE} =10V, I _C =10mA) | f _T | 100 | — | 300 | MHz |
| Output Capacitance 输出电容(V _{CB} =10V, I _E =0, f=1MHz) | C _{ob} | — | 6 | — | pF |

Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



| Dim | min | max |
|-----|----------|------|
| A | 1.40 | 1.60 |
| B | 0.40 | 0.56 |
| B1 | 0.35 | 0.48 |
| C | 0.35 | 0.44 |
| D | 4.40 | 4.60 |
| D1 | 1.35 | 1.83 |
| e | 1.50 BSC | |
| e1 | 3.00 BSC | |
| E | 2.29 | 2.60 |
| H | 3.75 | 4.25 |
| L | 0.80 | 1.20 |

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